

ABSTRACT

METAL OXIDE ETCHING SOLUTION COMPOSITION AND ETCHING METHOD

The object of the present invention is to provide an etching solution composition for etching a metal oxide containing In and a metal oxide containing Zn and In used as a transparent electrode or an oxide semiconductor of an electronic device, the etching solution composition being controllable to give a practical etching rate, having high dissolving power toward Zn, and enabling a long solution life due to suppressed variation of the formulation during use. The object is solved by an etching solution composition containing water and at least one type of acid, excluding hydrohalic acids, perhalic acids, etc., having an acid dissociation constant pK_{a_n} at 25°C in any dissociation stage of no greater than 2.15, and the composition having a pH at 25°C of no greater than 4, and an etching method using the etching solution composition.

[Selected drawing] None